

SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0007235 7

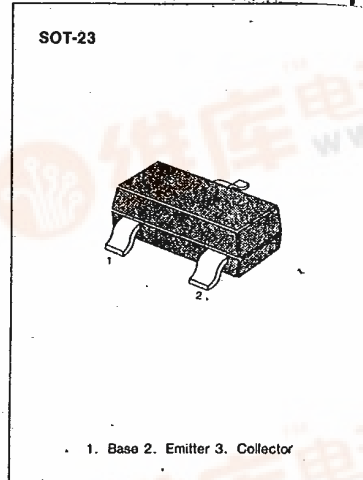
**MMBA812M6 PNP EPTAXIAL SILICON TRANSISTOR**

**GENERAL PURPOSE TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	50	V
Collector-Emitter Voltage	V <sub>CE0</sub>	40	V
Emitter-Base Voltage	V <sub>EB0</sub>	5	V
Collector Current	I <sub>C</sub>	100	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C

• Refer to MMBT5086 for graphs



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0		100	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0		100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	200	400	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =30mA, I <sub>B</sub> =3mA		0.5	V
Base-Emitter On Voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =1mA, V <sub>CE</sub> =6V		0.8	V

Marking

